

TRANSISTOR (PNP)

FEATURES

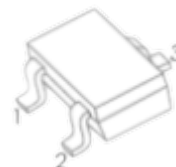
- Excellent h_{FE} linearity:

MARKING :AZG

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	833	$^\circ\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

1. BASE
2. EMITTER
3. COLLECTOR

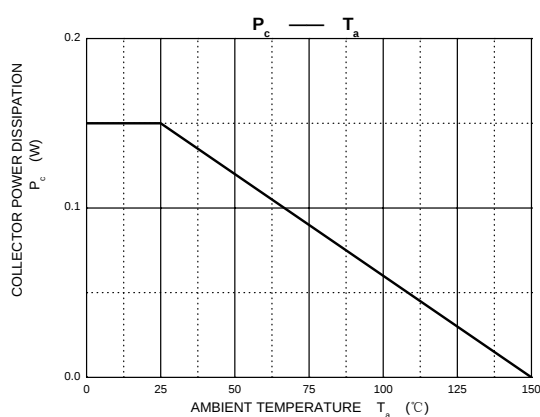
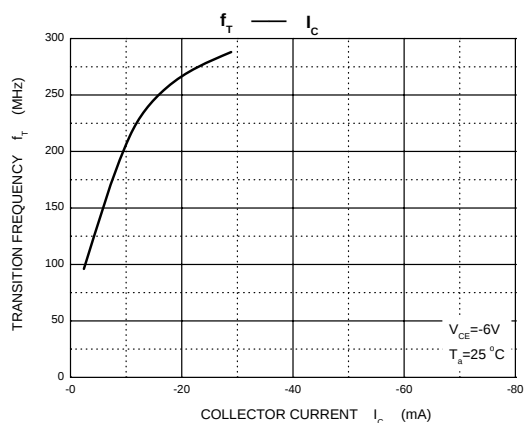
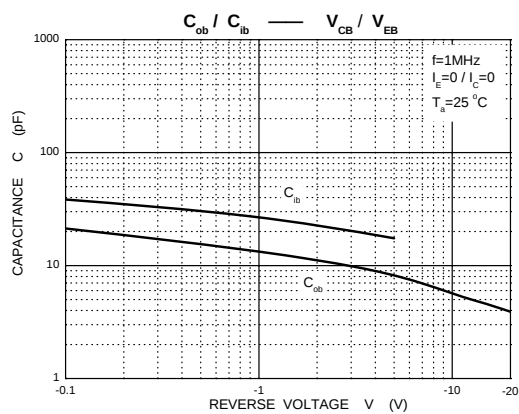
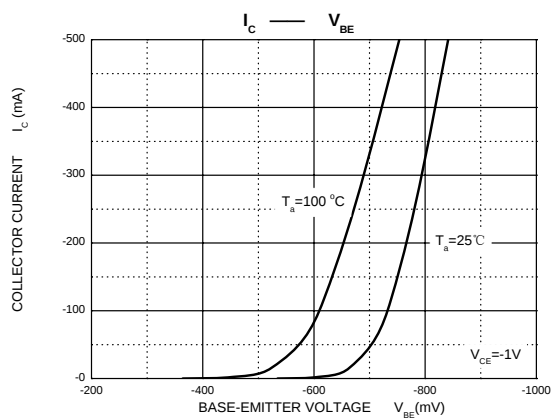
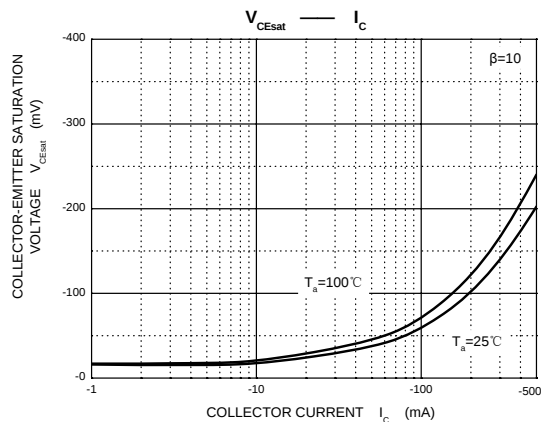
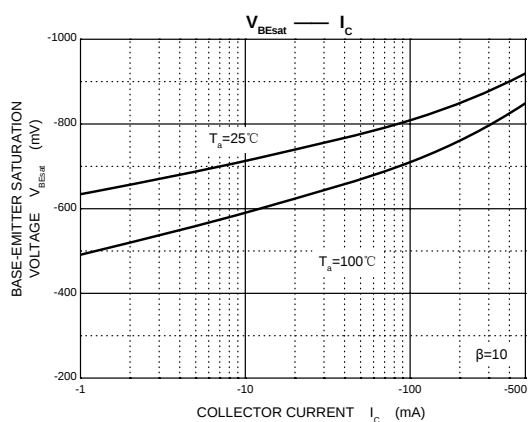
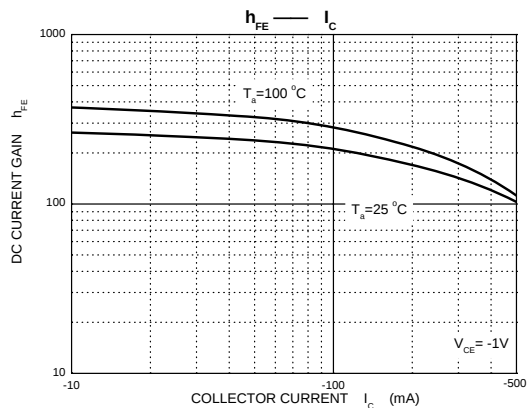
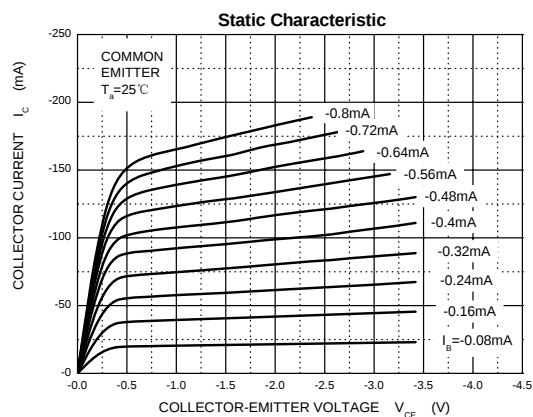


SOT-23

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	200		400	
	$h_{FE(2)}$	$V_{CE}=-6\text{V}, I_C=-400\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-6\text{V}, I_C=-20\text{mA}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0, f=1\text{MHz}$		13		pF

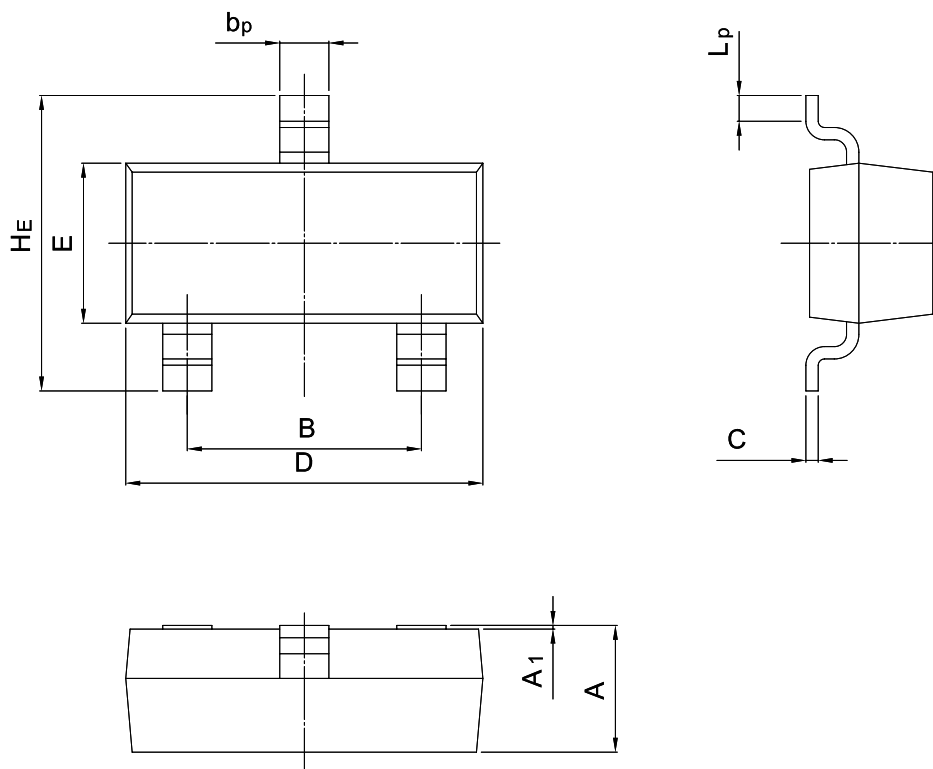
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20

